风光欣技术资料

A970

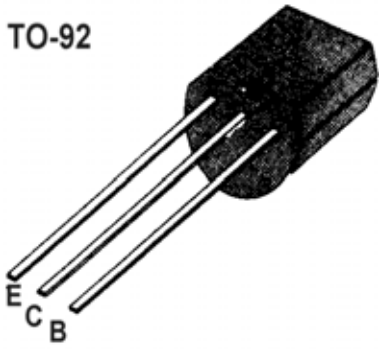
PNP Transistors

—PNP Silicon—

■■ **APPLICATION**：Low Noise Audio Amplifier Applications.

■■ **MAXIMUM RATINGS（Ta=25℃）**

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-120	V
Collector-emitter voltage	V_{CEO}	-120	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Baes current	I_B	-20	mA
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	Tj	125	℃
Storage Temperature Range	Tstg	-55~125	℃



■■ **ELECTRICAL CHARACTERISTICS**
（Ta=25℃，R_G=10KΩ）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV_{CBO}	-120			V	I_C=-0.1mA	I_E=0	
Collector-Emitter Breakdown Voltage	BV_{CEO}	-120			V	I_C=-1mA	I_B=0	
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	I_E=-0.1mA	I_C=0	
Collector Cut-off Current	I_{CBO}			-0.1	uA	V_{CB}=-120V	I_E=0	
Emitter Cut-off Current	I_{EBO}			-0.1	uA	V_{EB}=-5V	I_C=0	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	I_C=-10mA	I_B=-1mA	
Base-Emitter Voltage	V_{BE}		-0.65		V	V_{CE}=-6V	I_C=-2mA	
DC Current Gain	h_{FE}	200		700	β	V_{CE}=-6V	I_C=-2mA	
Gain bandwidth product	f_T		100		MHz	V_{CE}=-6V	I_C=-1mA	
Common Base Output Capacitance	Cob		4		pF	V_{CB}=-10V	I_E=0	f=1MHz
Noise Figure	NF			2	dB	V_{CE}=-6V	I_C=-0.1mA	f=1KHz

■■ **h_{FE} Classification And Marking**

Print Mark	A970	
Classification	GR	BL
h_{FE}	200~400	350~700